

Title (en)
OPTICAL SEMICONDUCTOR DIODE

Title (de)
OPTISCHE HALBLEITERDIODE

Title (fr)
DIODE OPTIQUE A SEMI-CONDUCTEUR

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Abstract (en)
[origin: WO0060675A1] The invention relates to an optical semiconductor diode (1) in which at least one intermediate layer (4) is positioned between an epitaxial layer stack (2) on a surface region (11) of a substrate (10) and said surface region. The intermediate layer contacts the surface region on its flat side such that it partly covers same and partly leaves it exposed and reflects a part (32) of a radiation (30) generated in the layer stack in the direction of the surface region.

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